RAMAN STUDY OF ION IMPLANTED AND PULSE LASER ANNEALED GALLIUM ARSENIDE

by
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DEDICATED TO

MY

BELOVED PARENTS

CERTIFICATE

This is to certify that the thesis entitled, "Raman Study of Ion Implanted and Pulse Laser Annealed Gallium Arsenide' being submitted by Mr. R. Ashokan for the award of the degree of 'Doctor of Philosophy', to the Indian Institute of Technology Delhi is a record of bonafide research work he has carried out under our guidance and supervision.

In our opinion, this thesis has reached the standard fulfilling the requirements of all regulations relating to the degree. The results contained in this thesis have not been submitted to any other University or Institute for the award of any degree or diploma.

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